

BCD TO DECIMAL DECODER

- **HIGH SPEED**
 $t_{PD} = 13 \text{ ns (TYP.) AT } V_{CC} = 5 \text{ V}$
- **LOW POWER DISSIPATION**
 $I_{CC} = 4 \mu\text{A (MAX.) AT } T_A = 25 \text{ }^\circ\text{C}$
- **HIGH NOISE IMMUNITY**
 $V_{NIH} = V_{NIL} = 28 \% V_{CC} \text{ (MIN.)}$
- **OUTPUT DRIVE CAPABILITY**
10 LSTTL LOADS
- **SYMMETRICAL OUTPUT IMPEDANCE**
 $|I_{OH}| = I_{OL} = 4 \text{ mA (MIN.)}$
- **BALANCED PROPAGATION DELAYS**
 $t_{PLH} = t_{PHL}$
- **WIDE OPERATING VOLTAGE RANGE**
 $V_{CC} \text{ (OPR)} = 2 \text{ V TO } 6 \text{ V}$
- **PIN AND FUNCTION COMPATIBLE**
WITH 54/74LS42

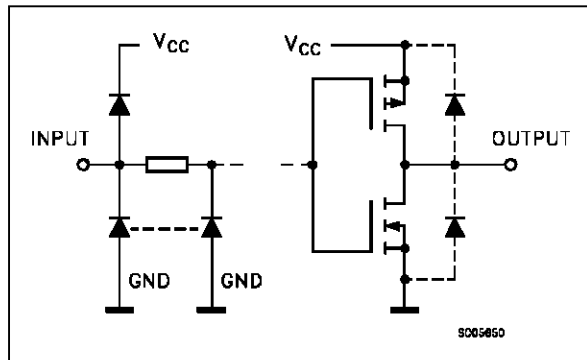
DESCRIPTION

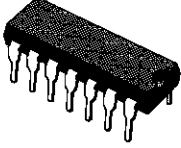
The M54/74HC42 is a high speed CMOS BCD-TO-DECIMAL DECODER fabricated in silicon gate C²MOS technology.

It has the same high speed performance of LSTTL combined with true CMOS low power consumption. A BCD code applied to the four inputs A-D selects one of ten decimal outputs $\overline{Y0}-\overline{Y9}$, which goes low to fifteen gives a high level at all outputs. This device also can be used as a 3-to-8 LINE DECODER, when the D input is assigned as a disable input. This device is useful for code conversion, address decoding, memory selection, demultiplexing, or readout decoding.

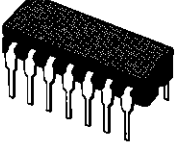
All inputs are equipped with protection circuits against static discharge and transient excess voltage.

INPUT AND OUTPUT EQUIVALENT CIRCUIT







B1R
(Plastic Package)



F1R
(Ceramic Package)



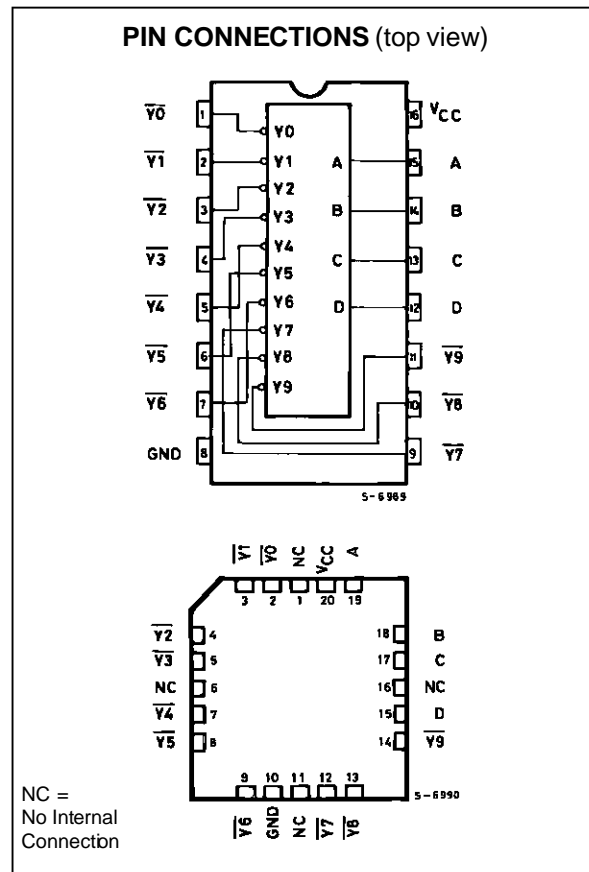
M1R
(Micro Package)



C1R
(Chip Carrier)

ORDER CODES :

M54HC42F1R	M74HC42M1R
M74HC42B1R	M74HC42C1R

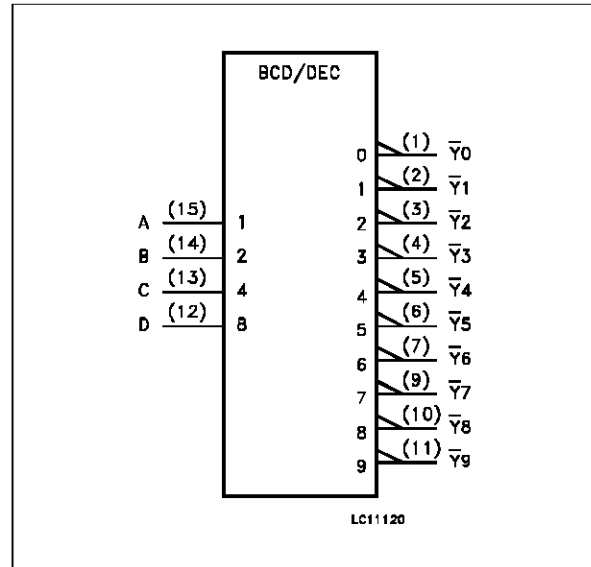


M54/M74HC42

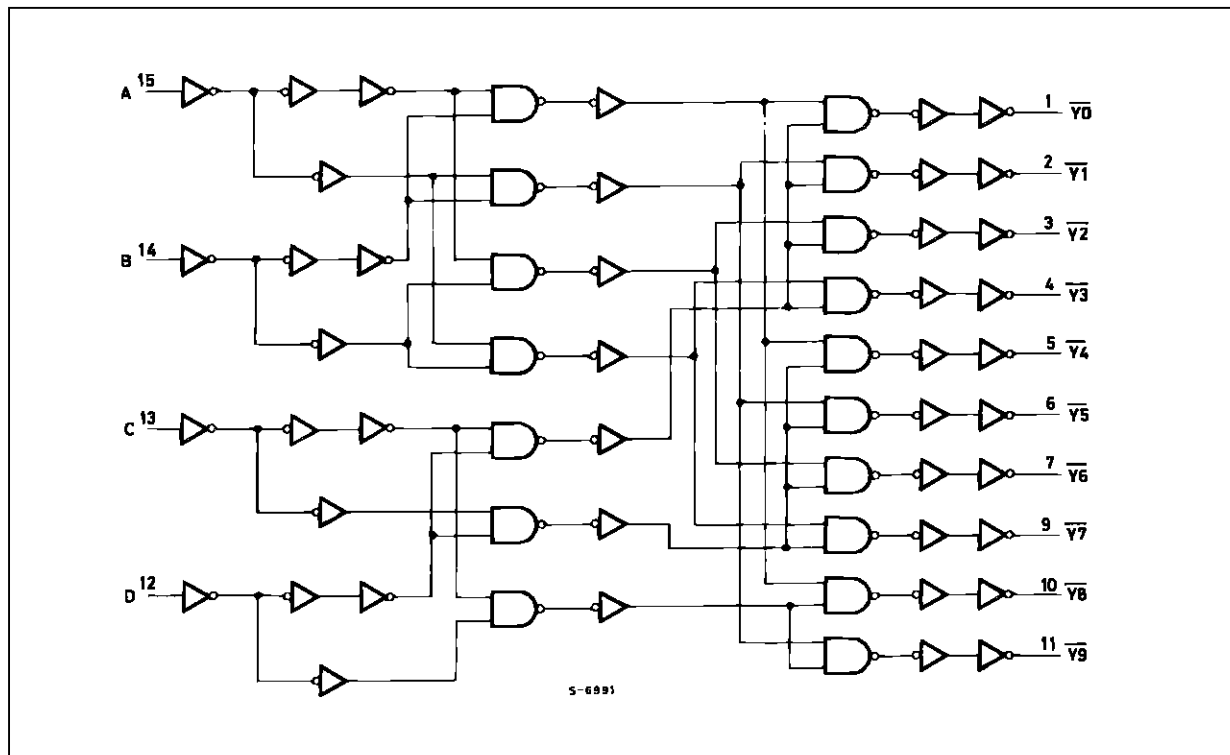
PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
15, 14, 13, 12	A, B, C, D	Data Inputs
1, 2, 3, 4, 5, 6, 7, 9, 10, 11	\bar{Y}_0 to \bar{Y}_9	Multiplexer Outputs
8	GND	Ground (0V)
16	V _{CC}	Positive Supply Voltage

IEC LOGIC SYMBOL



LOGIC DIAGRAM



FUNCTIONAL TABLE

CODE No.	BCD INPUTS				DECIMAL OUTPUTS									
	D	C	B	A	\bar{Y}_0	\bar{Y}_1	\bar{Y}_2	\bar{Y}_3	\bar{Y}_4	\bar{Y}_5	\bar{Y}_6	\bar{Y}_7	\bar{Y}_8	\bar{Y}_9
0	L	L	L	L	L	H	H	H	H	H	H	H	H	H
1	L	L	L	H	H	L	H	H	H	H	H	H	H	H
2	L	L	H	L	H	H	L	H	H	H	H	H	H	H
3	L	L	H	H	H	H	H	L	H	H	H	H	H	H
4	L	H	L	L	H	H	H	H	L	H	H	H	H	H
5	L	H	L	H	H	H	H	H	H	L	H	H	H	H
6	L	H	H	L	H	H	H	H	H	H	L	H	H	H
7	L	H	H	H	H	H	H	H	H	H	H	L	H	H
8	H	L	L	L	H	H	H	H	H	H	H	H	L	H
9	H	L	L	H	H	H	H	H	H	H	H	H	H	L
10	H	L	H	L	H	H	H	H	H	H	H	H	H	H
11	H	L	H	H	H	H	H	H	H	H	H	H	H	H
12	H	H	L	L	H	H	H	H	H	H	H	H	H	H
13	H	H	L	H	H	H	H	H	H	H	H	H	H	H
14	H	H	H	L	H	H	H	H	H	H	H	H	H	H
15	H	H	H	H	H	H	H	H	H	H	H	H	H	H

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CC}	Supply Voltage	-0.5 to +7	V
V_I	DC Input Voltage	-0.5 to $V_{CC} + 0.5$	V
V_O	DC Output Voltage	-0.5 to $V_{CC} + 0.5$	V
I_{IK}	DC Input Diode Current	± 20	mA
I_{OK}	DC Output Diode Current	± 20	mA
I_O	DC Output Source Sink Current Per Output Pin	± 25	mA
I_{CC} or I_{GND}	DC V_{CC} or Ground Current	± 50	mA
P_D	Power Dissipation	500 (*)	mW
T_{stg}	Storage Temperature	-65 to +150	°C
T_L	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these condition is not implied.

(*) 500 mW: \equiv 65 °C derate to 300 mW by 10mW/°C: 65 °C to 85 °C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit	
V_{CC}	Supply Voltage	2 to 6	V	
V_I	Input Voltage	0 to V_{CC}	V	
V_O	Output Voltage	0 to V_{CC}	V	
T_{op}	Operating Temperature: M54HC Series M74HC Series	-55 to +125 -40 to +85	°C °C	
t_r, t_f	Input Rise and Fall Time	$V_{CC} = 2 V$ $V_{CC} = 4.5 V$ $V_{CC} = 6 V$	0 to 1000 0 to 500 0 to 400	ns

M54/M74HC42

DC SPECIFICATIONS

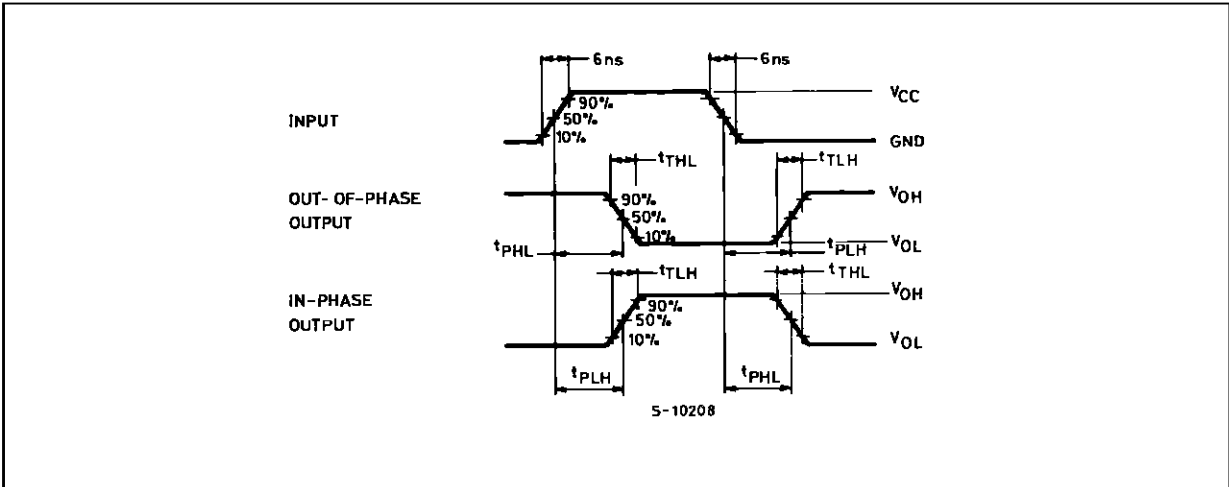
Symbol	Parameter	Test Conditions		Value						Unit		
		V _{CC} (V)		T _A = 25 °C 54HC and 74HC			-40 to 85 °C 74HC		-55 to 125 °C 54HC			
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.	
V _{IH}	High Level Input Voltage	2.0		1.5			1.5		1.5		V	
		4.5		3.15			3.15		3.15			
		6.0		4.2			4.2		4.2			
V _{IL}	Low Level Input Voltage	2.0				0.5		0.5		0.5	V	
		4.5				1.35		1.35		1.35		
		6.0				1.8		1.8		1.8		
V _{OH}	High Level Output Voltage	2.0	V _I = V _{IH} or V _{IL}	I _O = -20 μA	1.9	2.0		1.9		1.9	V	
		4.5			4.4	4.5		4.4		4.4		
		6.0			5.9	6.0		5.9		5.9		
		4.5		I _O = -4.0 mA	4.18	4.31		4.13		4.10		
		6.0			I _O = -5.2 mA	5.68	5.8		5.63			5.60
V _{OL}	Low Level Output Voltage	2.0	V _I = V _{IH} or V _{IL}	I _O = 20 μA		0.0	0.1		0.1		0.1	V
		4.5				0.0	0.1		0.1		0.1	
		6.0				0.0	0.1		0.1		0.1	
		4.5		I _O = 4.0 mA	0.17	0.26		0.33		0.40		
		6.0			I _O = 5.2 mA	0.18	0.26		0.33		0.40	
I _I	Input Leakage Current	6.0	V _I = V _{CC} or GND			±0.1		±1		±1	μA	
I _{CC}	Quiescent Supply Current	6.0	V _I = V _{CC} or GND			4		40		80	μA	

AC ELECTRICAL CHARACTERISTICS (C_L = 50 pF, Input t_r = t_f = 6 ns)

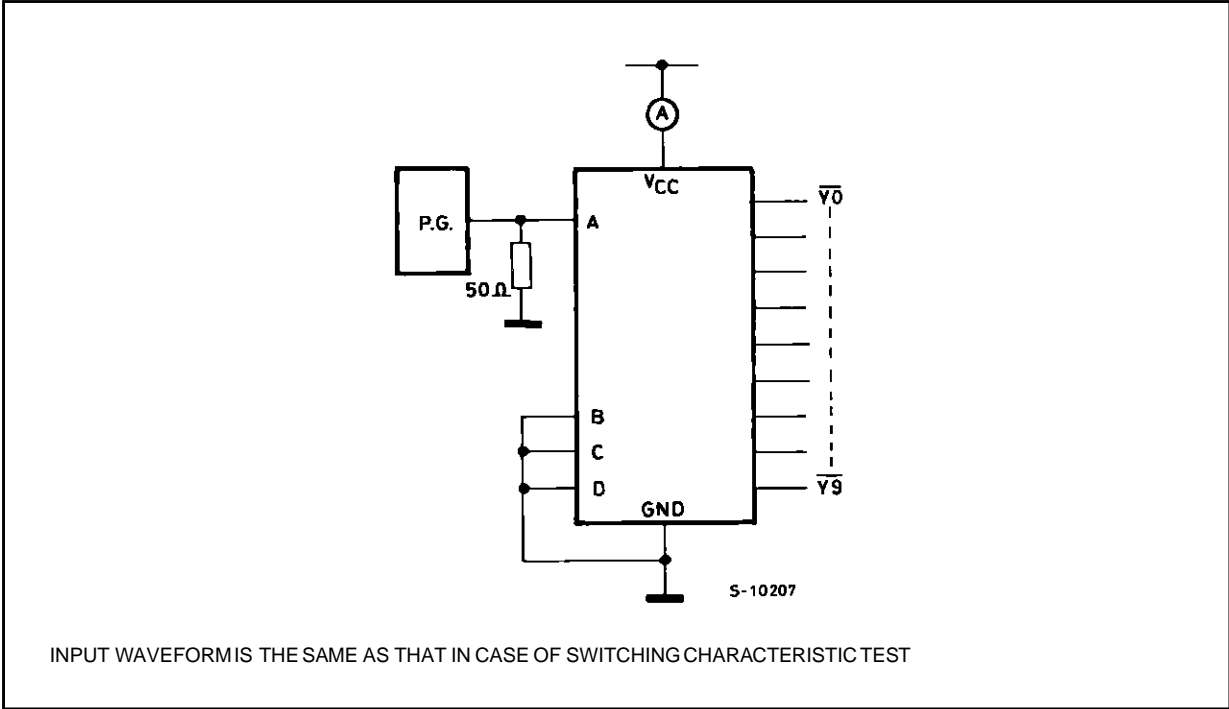
Symbol	Parameter	Test Conditions		Value						Unit	
		V _{CC} (V)		T _A = 25 °C 54HC and 74HC			-40 to 85 °C 74HC		-55 to 125 °C 54HC		
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.
t _{TLH} t _{THL}	Output Transition Time	2.0			30	75		95		110	ns
		4.5			8	15		19		22	
		6.0			7	13		16		19	
t _{PLH} t _{PHL}	Propagation Delay Time	2.0			64	130		165		195	ns
		4.5			16	26		33		39	
		6.0			14	22		28		33	
C _{IN}	Input Capacitance				5	10		10		10	pF
C _{PD} (*)	Power Dissipation Capacitance				60						pF

(*) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. I_{CC(opr)} = C_{PD} • V_{CC} • f_{IN} + I_{CC}

SWITCHING CHARACTERISTICS TEST WAVEFORM

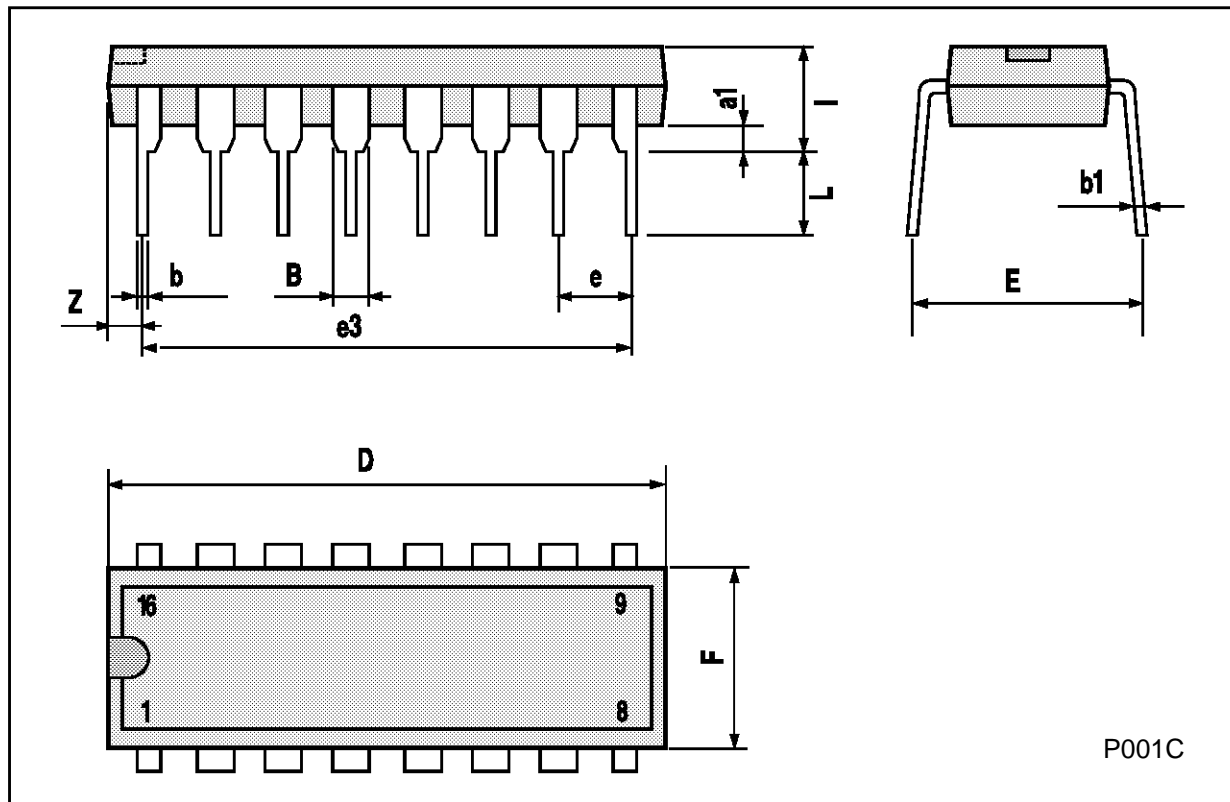


TEST CIRCUIT I_{cc} (Opr.)



Plastic DIP16 (0.25) MECHANICAL DATA

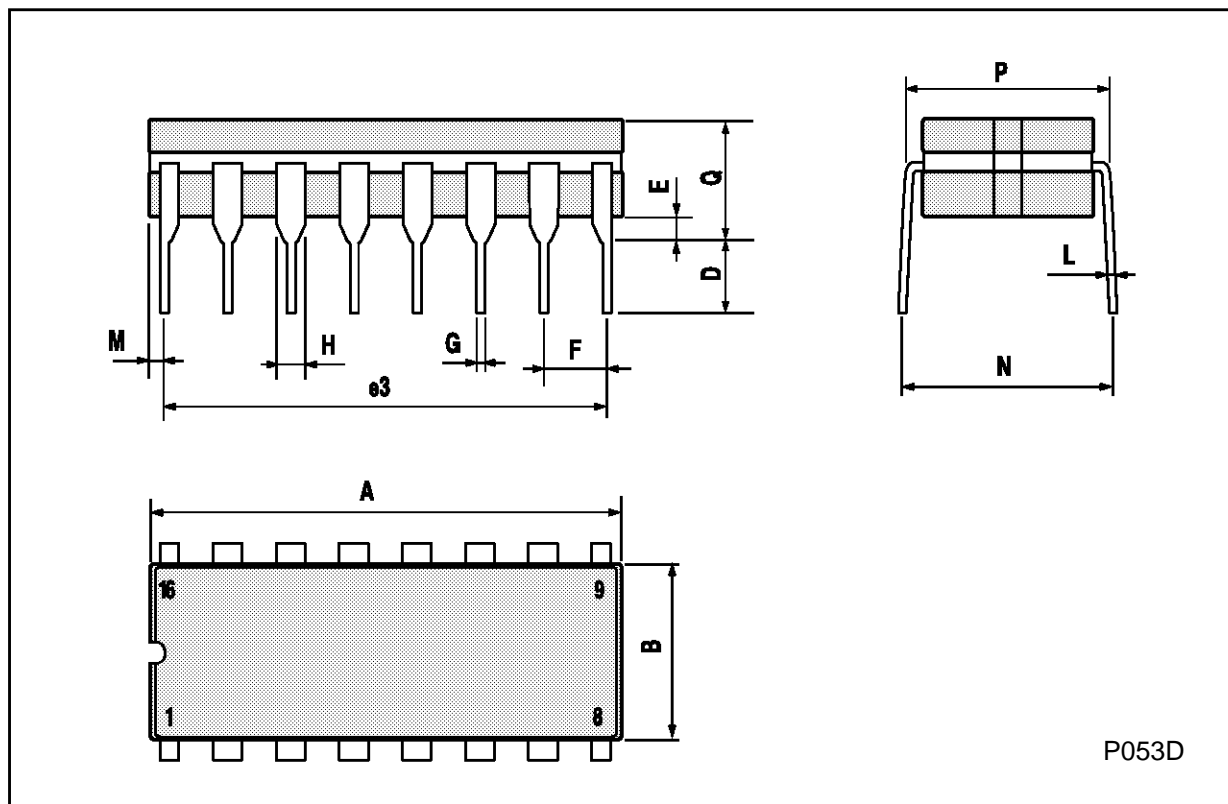
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
B	0.77		1.65	0.030		0.065
b		0.5			0.020	
b1		0.25			0.010	
D			20			0.787
E		8.5			0.335	
e		2.54			0.100	
e3		17.78			0.700	
F			7.1			0.280
I			5.1			0.201
L		3.3			0.130	
Z			1.27			0.050



P001C

Ceramic DIP16/1 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			20			0.787
B			7			0.276
D		3.3			0.130	
E	0.38			0.015		
e3		17.78			0.700	
F	2.29		2.79	0.090		0.110
G	0.4		0.55	0.016		0.022
H	1.17		1.52	0.046		0.060
L	0.22		0.31	0.009		0.012
M	0.51		1.27	0.020		0.050
N			10.3			0.406
P	7.8		8.05	0.307		0.317
Q			5.08			0.200



SO16 (Narrow) MECHANICAL DATA

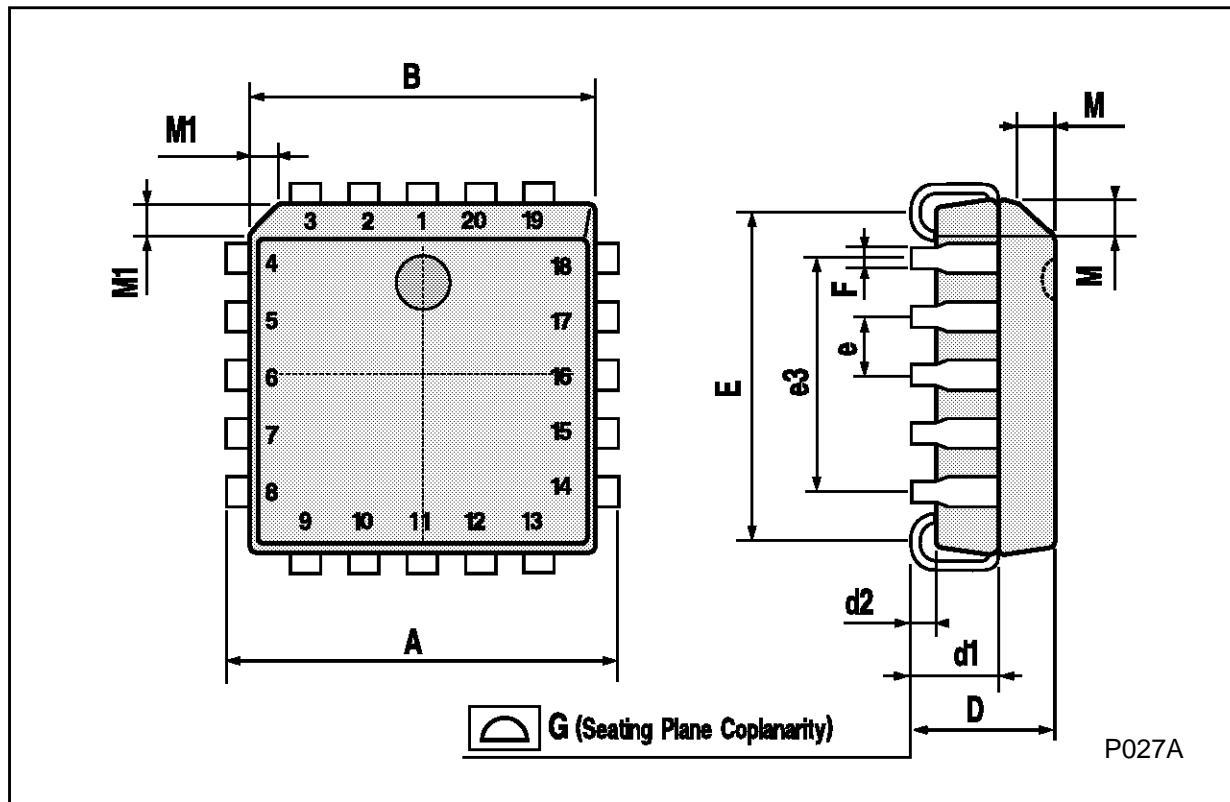
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.2	0.004		0.007
a2			1.65			0.064
b	0.35		0.46	0.013		0.018
b1	0.19		0.25	0.007		0.010
C		0.5			0.019	
c1	45° (typ.)					
D	9.8		10	0.385		0.393
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		8.89			0.350	
F	3.8		4.0	0.149		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.019		0.050
M			0.62			0.024
S	8° (max.)					



P013H

PLCC20 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	9.78		10.03	0.385		0.395
B	8.89		9.04	0.350		0.356
D	4.2		4.57	0.165		0.180
d1		2.54			0.100	
d2		0.56			0.022	
E	7.37		8.38	0.290		0.330
e		1.27			0.050	
e3		5.08			0.200	
F		0.38			0.015	
G			0.101			0.004
M		1.27			0.050	
M1		1.14			0.045	



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